

## DB101S thru DB107S



Unit : inch (mm)

.016)

060(~

04(0.

.009(0.25

σ

310(7

089(2.5)

.335(8.51)

.316(8.05)

.045(1.14)

205(5.2) 195(5.0)

Pb Free Plating Product

1.0 Ampere Surface Mount Glass Passivated Bridge Rectifier

DB-S/DF-S

.360(9.40) .255(6.5) .245(6.2)

410(10.4)

## **Features**

- Glass passivated chip junction
- Low forward voltage drop
- High surge overload rating of 50 A peak
- Ideal for printed circuit board

## **Mechanical Data**

- Case: Molded plastic, DB-S/DF-S
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Leads solderable per MIL-STD-202, method 208 guaranteed
- Mounting position: Any

## Absolute Maximum Ratings and Characteristics

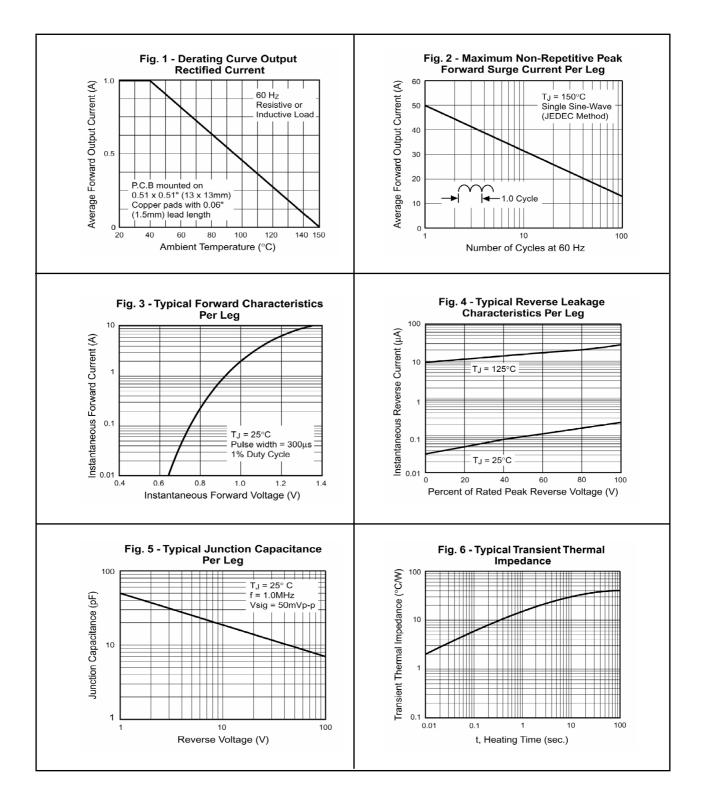
Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter		c .	S DB102S S DF01S	DB103S DF02S		DB105S DF06S	DB106S DF08S	DB107S DF10S	Unit
Maximum Recurrent Peak Reverse Voltage		50	100	200	400	600	800	1000	V
Maximum RMS Voltage		35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage		50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_A$ = 40 °C			1						
Peak Forward Surge Current 8.3 ms Single Half-sine-wave Superimposed on Rated Load (JEDEC Method)			50						А
Maximum Forward Voltage at 1 A			1.1						V
Maximum Reverse Current at Ratedat $T_A = 25^{\circ}$ DC Blocking Voltageat $T_A = 125^{\circ}$			5 500					μA	
Typical Junction Capacitance <sup>1)</sup>			25						pF
Typical Thermal Resistance <sup>2)</sup>			40						°C/W
Typical Thermal Resistance <sup>2)</sup>			15						°C/W
Operating and Storage Temperature Range		5	-55 to +150						°C

<sup>1)</sup> Measured at 1 MHz and applied reverse voltage of 4 V

<sup>2)</sup> Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B with 0.5 X 0.5" (13 X 13 mm) copper pads.





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